



INTERNATIONAL STANDARD

**Semiconductor devices – Semiconductor devices for energy harvesting and generation –
Part 6: Test and evaluation methods for vertical contact mode triboelectric energy harvesting devices**

INTERNATIONAL
ELECTROTECHNICAL
COMMISSION

ICS 31.080.99

ISBN 978-2-8322-7165-0

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International Standard IEC 62830-6 has been prepared by IEC technical committee 47: Semiconductor devices.

The text of this standard is based on the following documents:

FDIS	Report on voting
47/2573/FDIS	47/2585/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 62830 series, published under the general title *Semiconductor devices – Semiconductor devices for energy harvesting and generation*, can be found on the IEC website.

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A bilingual version of this publication may be issued at a later date.

SEMICONDUCTOR DEVICES – SEMICONDUCTOR DEVICES FOR ENERGY HARVESTING AND GENERATION –

Part 6: Test and evaluation methods for vertical contact mode triboelectric energy harvesting devices

1 Scope

This part of IEC 62830 defines terms, definitions, symbols, and specifies configurations and test methods to be used to evaluate and determine the performance characteristics of vertical contact mode triboelectric energy harvesting devices for practical use. This document is applicable to energy harvesting devices as power sources for wearable devices and wireless sensors used in healthcare monitoring, consumer electronics, general industries, military and aerospace applications without any limitations on device technology and size.

2 Normative references

There are no normative references in this document.